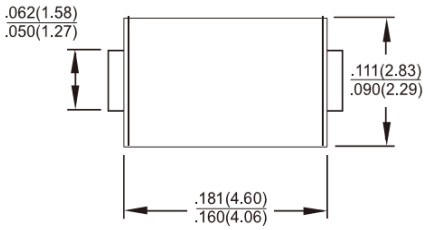
TAIWAN SEMICONDUCTOR

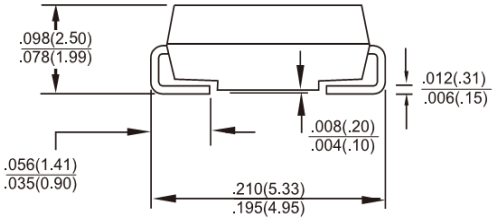
Pb RoHS COMPLIANCE

RS1A - RS1M

1.0 AMP. Surface Mount Fast Recovery Rectifiers

SMA/DO-214AC





Features

- ✧ For surface mounted application
- ✧ Glass passivated junction chip
- ✧ Built-in strain relief, ideal for automated placement
- ✧ Plastic material used carries Underwriters Laboratory Classification 94V-0
- ✧ Fast switching for high efficiency
- ✧ High temperature soldering: 260℃ / 10 seconds at terminals
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode

Mechanical Data

- ✧ Case: Molded plastic
- ✧ Terminals: Pure tin plated, Lead free
- ✧ Polarity: Indicated by cathode band
- ✧ Packing: 12mm tape per EIA STD RS-481
- ✧ Weight: 0.064 grams

Dimensions in inches and (millimeters)

Marking Diagram

RS1X	= Specific Device Code
G	= Green Compound
Y	= Year
M	= Work Month

Maximum Ratings and Electrical Characteristics

Rating at 25 ℃ ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	RS 1A	RS 1B	RS 1D	RS 1G	RS 1J	RS 1K	RS 1M	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current .375 (9.5mm) Lead Length @ T_L=90℃	$I_{F(AV)}$	1							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	30							A
Maximum Instantaneous Forward Voltage (Note 1) @ 1 A	V_F	1.3							V
Maximum Reverse Current @ Rated VR T_A=25 ℃ T_A=125 ℃	I_R	5 50							uA
Maximum Reverse Recovery Time (Note 2)	Trr	150				250	500		nS
Typical Junction Capacitance (Note 3)	Cj	10							pF
Typical Thermal Resistance	$R_{\theta jA}$ $R_{\theta jC}$	105 32							^{O}C/W
Operating Temperature Range	T_J	- 55 to + 150							^{O}C
Storage Temperature Range	T_{STG}	- 55 to + 150							^{O}C

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES (RS1A THRU RS1M)

FIG.1 FORWARD CURRENT DERATING CURVE

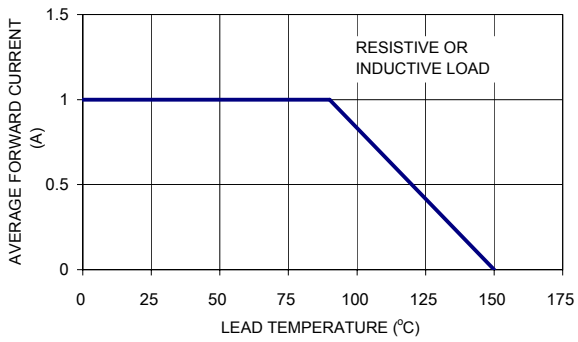


FIG. 2 TYPICAL REVERSE CHARACTERISTICS

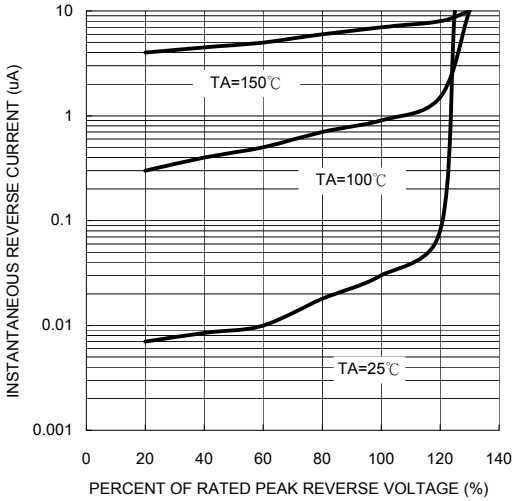


FIG. 3 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

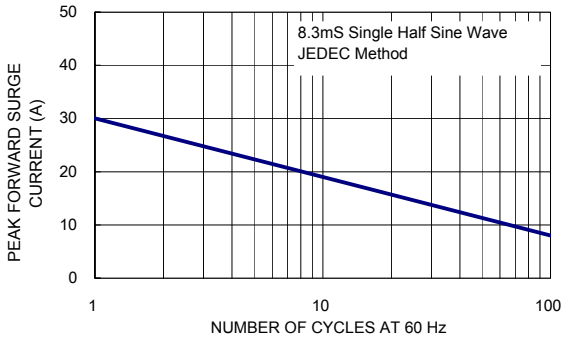


FIG. 5 TYPICAL FORWARD CHARACTERISRICS

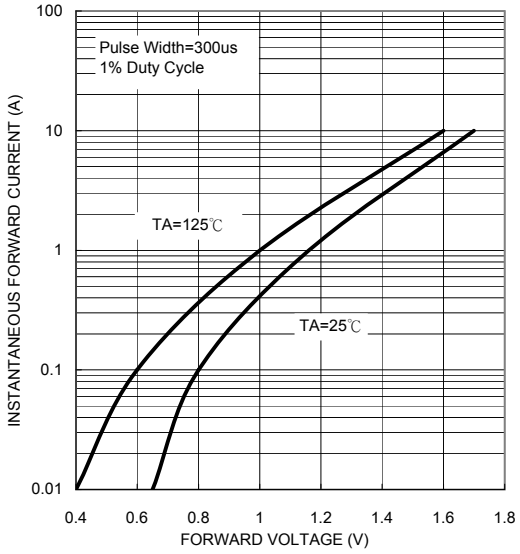


FIG. 4 TYPICAL JUNCTION CAPACITANCE

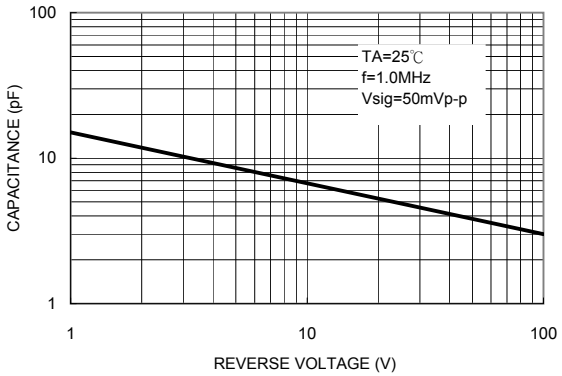


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM